

Application No.: 09/893,557

Docket No.: 8733.475.00-US

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended): A reflective liquid crystal display device comprising:
 - a plurality of gate lines and data lines intersecting on a first substrate, the gate line and the data line defining pixel areas;
 - a plurality of thin film transistors formed at the intersections of the gate lines and the data lines, each thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;
 - a capacitor lower electrode of a storage capacitor formed on the same plane as a gate line;
 - a capacitor upper electrode formed integrally with the drain electrode on the capacitor lower electrode;
 - a first gate insulation film inserted between the capacitor upper electrode and the capacitor lower electrode;
 - a passivation film between the capacitor upper electrode and the reflective electrode; and
 - ~~a thin film transistor array substrate connected with the drain electrode and including a~~ reflective electrode formed over the passivation film at the pixel areas ~~and formed above and~~ electrically connected to the drain electrode through a contact hole in the passivation film.
2. (Currently Amended): The reflective liquid crystal display as claimed in claim 1, wherein the first gate insulation film is one of silicon nitride(SiNx) and silicon oxide(SiOx).
3. (Canceled):

Application No.: 09/893,557

Docket No.: 8733.475.00-US

4. (Currently Amended): The reflective liquid crystal display as claimed in claim 3 ~~1~~, wherein the ~~second insulation~~ passivation film is one of silicone nitride (SiNx), BCB and acrylic resin.

5. (Currently Amended): A transfective liquid crystal display device, which has pixel areas defined into a reflection part and a transmission part, the liquid crystal display device comprising:

a plurality of gate lines and data lines intersecting on a ~~first~~ substrate, the gate line and the data line defining pixel areas;

a plurality of thin film transistors formed at the intersections of the gate lines and the data lines, each thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

a capacitor lower electrode of a storage capacitor formed on the same plane as a gate line;

a capacitor upper electrode formed integrally with the drain electrode on the capacitor lower electrode;

a ~~first gate~~ insulation film inserted between the capacitor upper electrode and the capacitor lower electrode;

a first passivation film between the capacitor upper electrode and the reflective electrode;
and

a reflective electrode electrically connected with the drain electrode through a contact hole in the first passivation film and formed over the first passivation film on the reflection area above the drain electrode at the reflection part; and ,

Application No.: 09/893,557

Docket No.: 8733.475.00-US

~~a thin film transistor array substrate connected with the reflective electrode and including~~
wherein the pixel area includes the transmissive electrode formed at the transmission area part.

6. (Original): The transflective liquid crystal display device as claimed in claim 5, wherein the capacitor upper electrode extends along a boundary part between the reflective electrode and the transmissive electrode to prevent light leakage.

7. (Currently Amended): The transflective liquid crystal display device as claimed in claim 5, wherein the ~~first~~ gate insulation film is one of silicone nitride(SiNx) and silicon oxide(SiOx).

8. (Canceled):

9. (Currently Amended): The transflective liquid crystal display device as claimed in claim 8 5, wherein the second insulation film is one of silicon nitride (SiNx), BCB or acryl resin.

10. (Currently Amended): The transflective liquid crystal display device as claimed in claim 5, further comprising ~~another first insulation~~ a second passivation film between the reflective electrode and the transmissive electrode.

11. (Withdrawn): A method for manufacturing a reflective liquid crystal display device, the method comprising:

intersecting a plurality of gate lines and data lines on a first substrate;

Application No.: 09/893,557

Docket No.: 8733.475.00-US

forming a thin film transistor on the intersection of the gate line and the data line, the thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

forming a capacitor lower electrode of a storage capacitor on the same plane as the gate line;

forming an insulation film on the capacitor lower electrode;

forming an capacitor upper electrode on an upper portion of the capacitor lower electrode, the capacitor upper electrode being formed integrally with the drain electrode; and

forming a reflective electrode connected with the drain electrode.

12. (Withdrawn): A method for manufacturing a transfective liquid crystal display device, which has pixel areas defined into a reflection part and a transmission part, the method comprising: intersecting a plurality of gate lines and data lines on a first substrate;

forming a thin film transistor on the intersection of the gate line and the data line, the thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

forming a capacitor lower electrode of a storage capacitor on the same plane as the gate line;

forming an insulation film on the capacitor lower electrode;

forming a capacitor upper electrode on an upper portion of the capacitor lower electrode, the capacitor upper electrode being formed integrally with the drain electrode;

forming a reflective electrode connected with the drain electrode at the reflection area;

and

Application No.: 09/893,557

Docket No.: 8733.475.00-US

forming a transfective electrode connected with the reflective electrode at the transmission area.

13. (New): The reflective liquid crystal display as claimed in claim 1, wherein the gate electrode and the capacitor upper electrode are of metal.

14. (New): The reflective liquid crystal display as claimed in claim 13, wherein the gate electrode is selected from the group consisting of chrome, molybdenum, aluminum, tin, copper and combinations thereof.

15. (New): The reflective liquid crystal display as claimed in claim 13, wherein the capacitor upper electrode is aluminum or aluminum alloy.

16. (New): The transfective liquid crystal display device as claimed in claim 5, wherein the gate electrode and the capacitor upper electrode are of metal.

17. (New): The transfective liquid crystal display device as claimed in claim 16, wherein the gate electrode is selected from the group consisting of chrome, molybdenum, aluminum, tin, copper and combinations thereof.

18. (New): The transfective liquid crystal display device as claimed in claim 16, wherein the capacitor upper electrode is aluminum or aluminum alloy.

Application No.: 09/893,557

Docket No.: 8733.475.00-US

19. (New): The transfective liquid crystal display device as claimed in claim 5, wherein the reflective electrode is electrically connected to the transmissive electrode through the second passivation film.